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**1N17
THRU
1N19**

Features

- Lead Free Finish/RoHS Compliant(Note 1)
- High Efficiency and High Current Capability
- Low Forward Voltage Drop and Low Power loss
- Metal Silicon junction, majority carrier conduction
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1
- Marking : Cathode band and type number

Maximum Ratings

- Operating Temperature: -55°C to +125°C
- Storage Temperature: -55°C to +125°C
- Typical Thermal Resistance: 50°C/W junction to Ambient
- For capacitive load. Derate current by 20%

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
1N17	20V	14V	20V
1N18	30V	21V	30V
1N19	40V	28V	40V

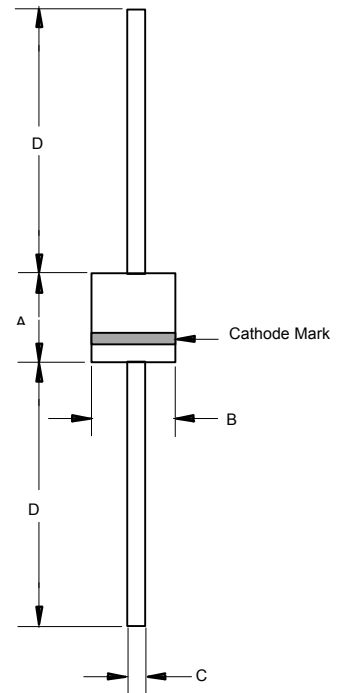
Electrical Characteristics @ 25°C Unless Otherwise Specified

Average Forward Rectified Current	I_{AV}	1.0A	$T_A = 90^\circ\text{C}$
Peak Forward Surge Current	I_{FSM}	25A	8.3ms, half sine
Maximum Instantaneous Forward Voltage	V_F	0.45V 0.55V 0.60V	$I_{FM} = 1.0\text{A};$ $T_C = 25^\circ\text{C}$
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	0.5mA 10mA	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$
Typical Junction Capacitance	C_J	110pF	Measured at 1.0MHz, $V_R=4.0\text{V}$

Notes:1.High Temperature Solder Exemption Applied, see EU Directive Annex 7.

**1.0 Amp Schottky
Barrier Rectifier
20 to 40 Volts**

R-1



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.116	0.140	2.90	3.50	
B	0.091	0.102	2.30	2.60	
C	0.020	0.024	0.50	0.60	
D	0.787	-----	20.00	-----	

1N17 thru 1N19



FIG.1-FORWARD CURRENT DERATING CURVE

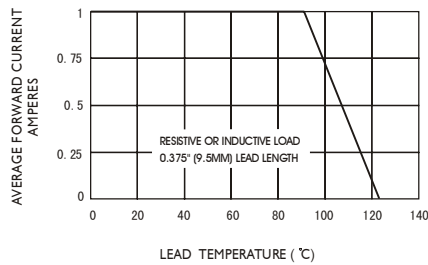


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

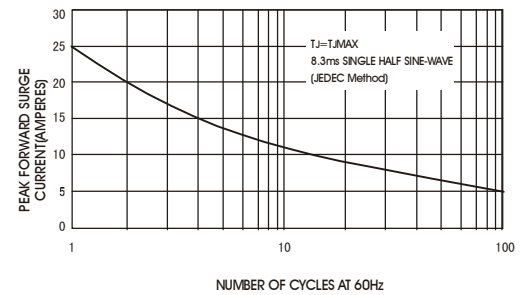


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

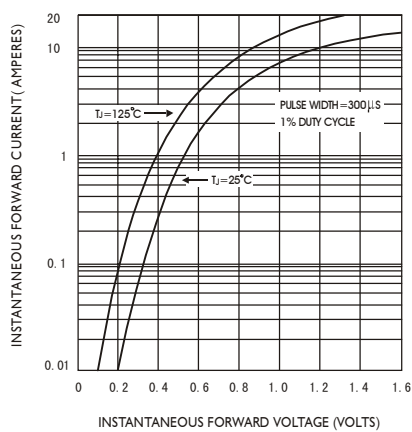


FIG.4-TYPICAL REVERSE CHARACTERISTICS

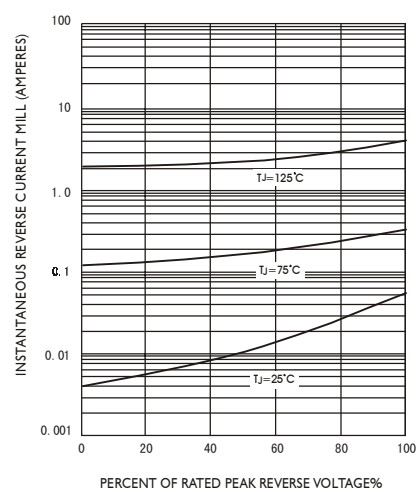


FIG.5-TYPICAL JUNCTION CAPACITANCE

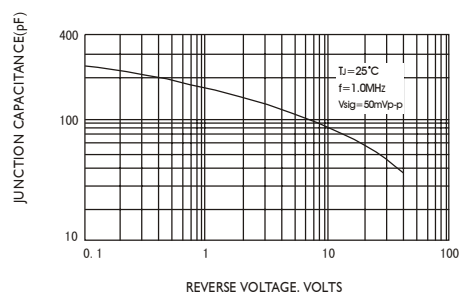


FIG.6-TYPICAL TRANSIENT THERMAL IMPEDANCE

